

MOSFET – Power, N-Channel With ESD Protection 60 V, 853 mA

NVNJWS1K6N061L

Features

- Low $R_{DS(on)}$ and Low Gate Threshold
- Low Input Capacitance
- ESD Protected Gate
- Wettable Flank for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- This is a Pb-Free Device

Applications

- Low Side Load Switch
- DC-DC Converters (Buck and Boost Circuits)

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	60	V	
Gate-to-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	I_D	853	mA
		$T_C = 100^\circ\text{C}$		603	
Power Dissipation $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	P_D	2617	mW
		$T_C = 100^\circ\text{C}$		1309	
Continuous Drain Current $R_{\theta JA}$ (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	I_D	632	mA
		$T_A = 100^\circ\text{C}$		447	
Power Dissipation $R_{\theta JA}$ (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	P_D	1437	mW
		$T_A = 100^\circ\text{C}$		718	
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	I_{DM}	6.47	A	
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 175	$^\circ\text{C}$	
Source Current (Body Diode)		I_S	2.181	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

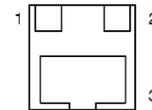
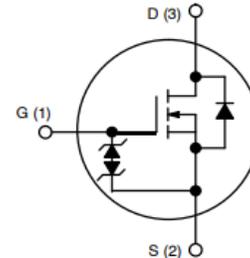
THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Ambient – Steady State	$R_{\theta JA}$	104	$^\circ\text{C}/\text{W}$
Junction-to-Case – Steady State	$R_{\theta JC}$	57.31	

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).

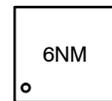
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D Max
60 V	1.6 Ω @ 10 V	853 mA
	2.5 Ω @ 4.5 V	

N-CHANNEL MOSFET



XDFNW3
CASE 521AC

MARKING DIAGRAM



6N = Specific Device Code
M = Month Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

NVNJWS1K6N061L

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\ \mu\text{A}$, ref to 25°C		87		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 60\text{ V}$			1.0	μA
					500	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 10	μA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	1.0		2.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-4.3		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 500\text{ mA}$		1.2	1.6	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 200\text{ mA}$		1.5	2.5	
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 200\text{ mA}$		0.48		S

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 20\text{ V}$		26		pF
Output Capacitance	C_{OSS}			4.4		
Reverse Transfer Capacitance	C_{RSS}			2.5		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 25\text{ V}, I_D = 200\text{ mA}$		0.9		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.2		
Gate-to-Source Charge	Q_{GS}			0.3		
Gate-to-Drain Charge	Q_{GD}			0.28		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 4.5\text{ V}, V_{DD} = 25\text{ V}, I_D = 200\text{ mA}, R_G = 25\ \Omega$		22		ns
Rise Time	t_r			34		
Turn-Off Delay Time	$t_{d(off)}$			34		
Fall Time	t_f			32		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 200\text{ mA}$	$T_J = 25^\circ\text{C}$		0.8	1.2	V
			$T_J = 125^\circ\text{C}$		0.64		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

3. Switching characteristics are independent of operating junction temperatures.

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TYPICAL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)

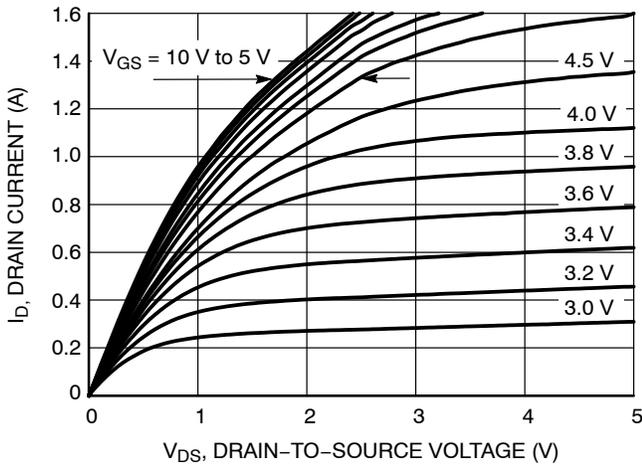


Figure 1. On-Region Characteristics

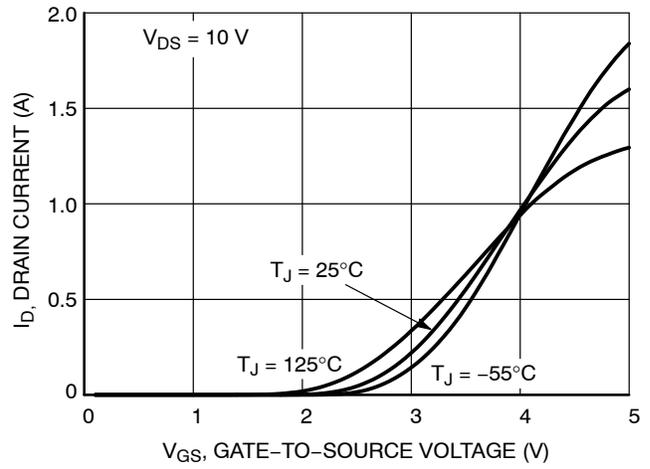


Figure 2. Transfer Characteristics

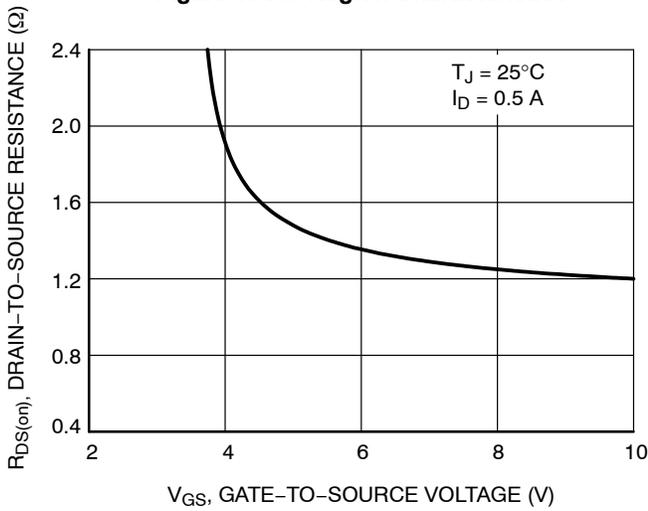


Figure 3. On-Resistance vs. Gate-to-Source Voltage

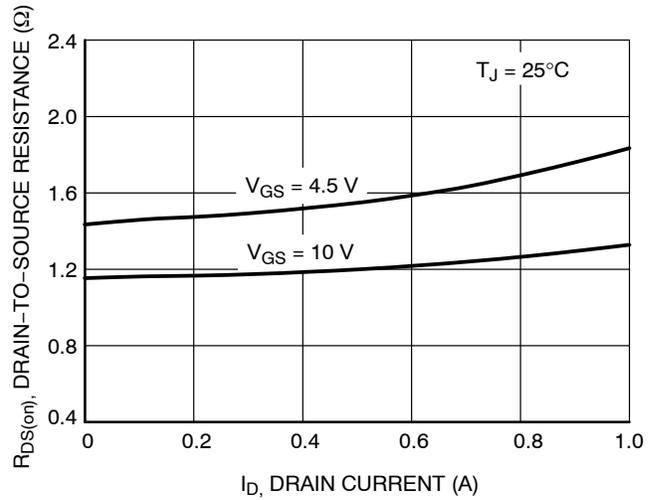


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

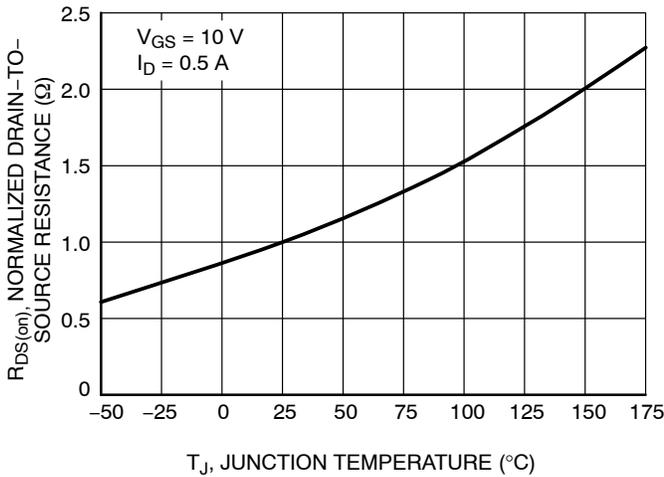


Figure 5. On-Resistance Variation with Temperature

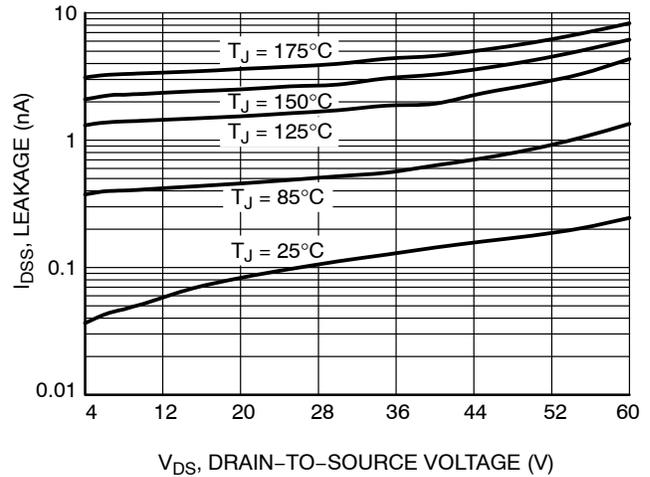


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)

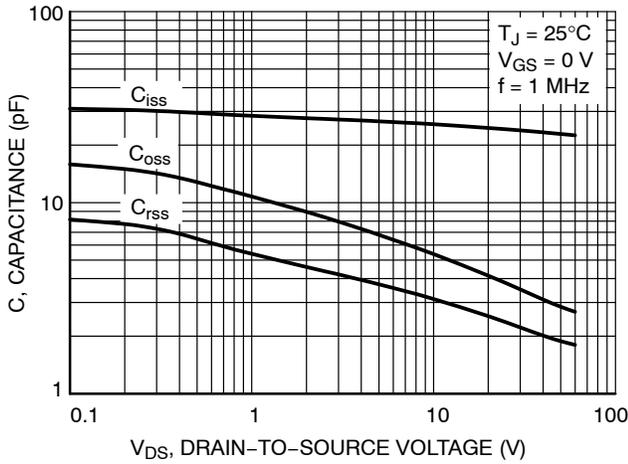


Figure 7. Capacitance Variation

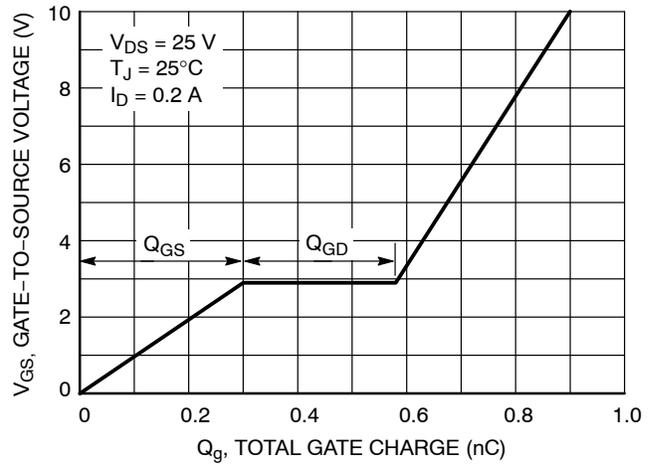


Figure 8. Gate-to-Source vs. Total Charge

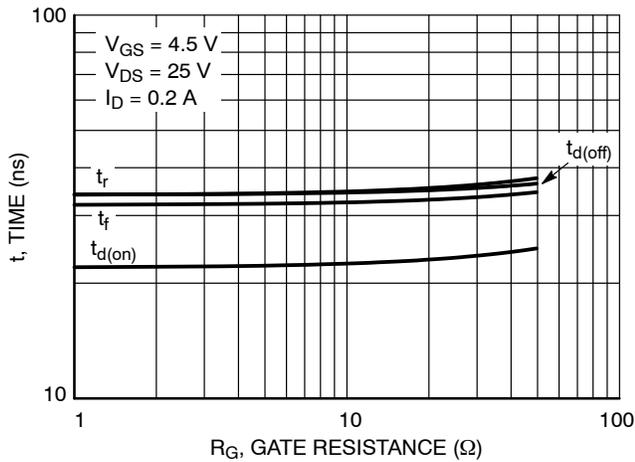


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

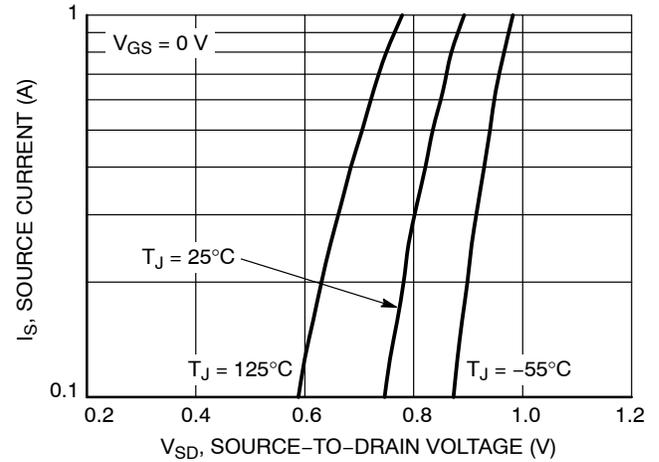


Figure 10. Diode Forward Voltage vs. Current

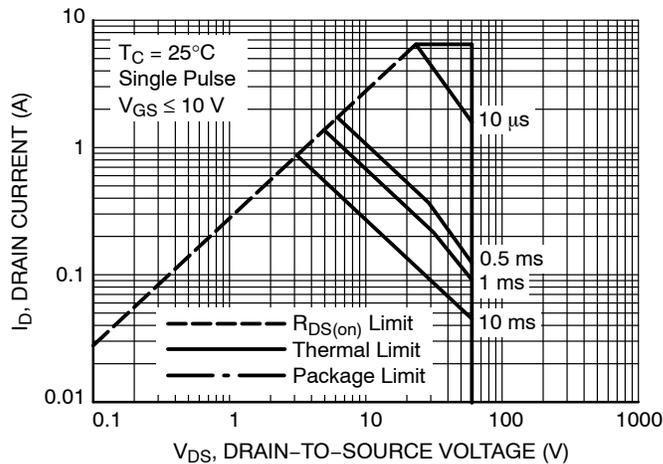


Figure 11. Maximum Rated Forward Biased Safe Operating Area

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TYPICAL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)

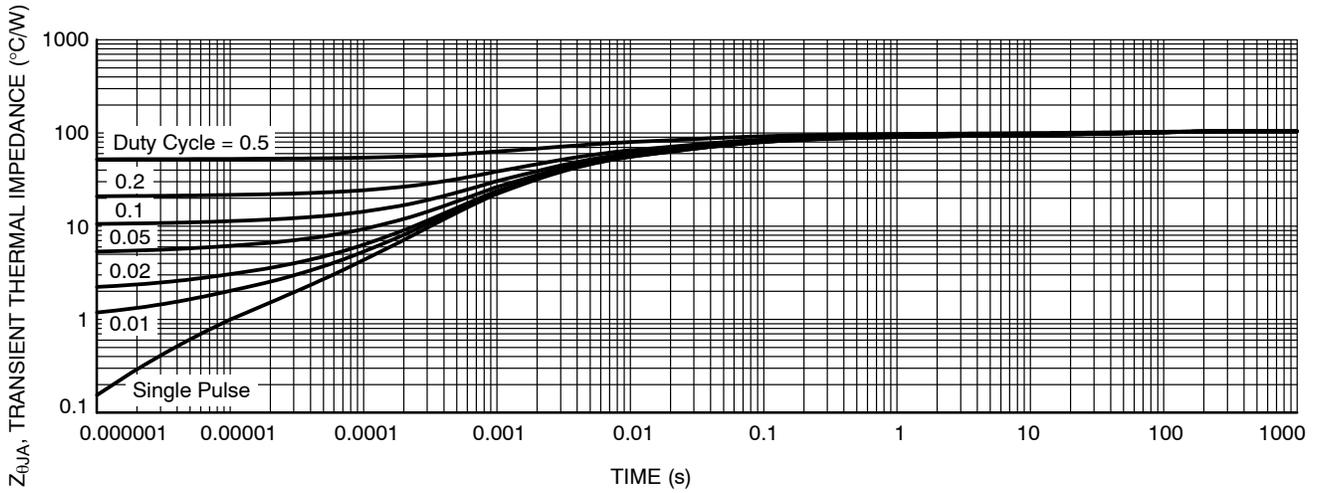


Figure 12. Junction-to-Case Transient Thermal Response

Table 1. ORDERING INFORMATION

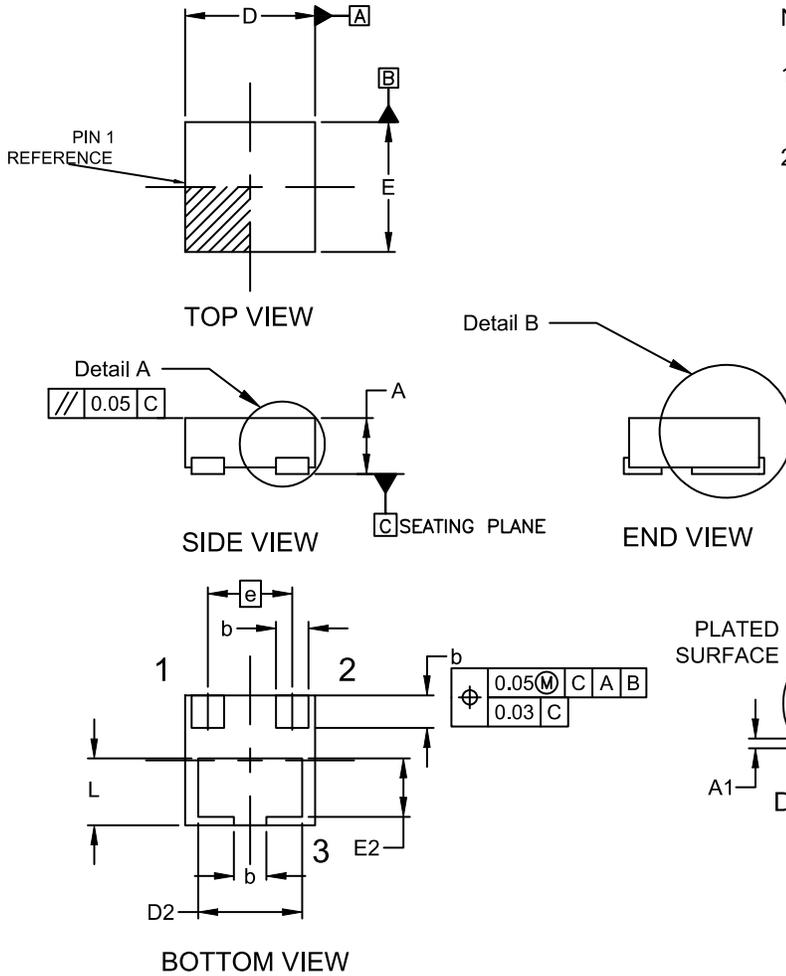
Part Number	Marking	Package	Shipping [†]
NVNJWS1K6N061LTAG	6N	XDFNW3 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NVNJWS1K6N061L

PACKAGE DIMENSIONS

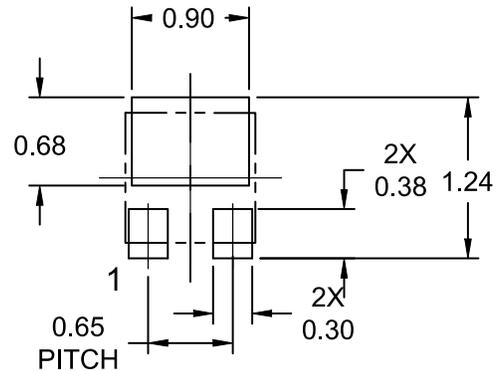
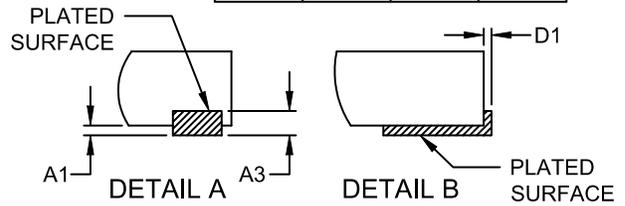
XDFNW3 1x1, 0.65P
CASE 521AC
ISSUE A



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.32	0.38	0.44
A1	0.00	---	0.04
A3	0.125 REF		
b	0.20	0.25	0.30
D	0.90	1.00	1.10
D1	0.00	---	0.04
D2	0.75	0.80	0.85
E	0.90	1.00	1.10
E2	0.40	0.45	0.50
e	0.65 BSC		
L	0.465	0.515	0.565



RECOMMENDED MOUNTING FOOTPRINT*

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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